NSN 5961-01-395-0026

Transistor - Page 1 of 1

Demilitarization:

No Fiig: A110a0



View Online at https://aerobasegroup.com/nsn/5961-01-395-0026 **Inclosure Material:** Ceramic **Overall Length:** 0.933 inches **Overall Height:** 0.375 inches **Overall Width:** 0.415 inches **Mounting Facility Quantity: Internal Configuration:** Field effect Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-257 **Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 500.0 drain to source voltage and 16.0 gate to source voltage **Current Rating Per Characteristic:** 4.50 amperes drain current **Power Rating Per Characteristic:** 50.0 watts total device dissipation **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Special Features:** Contains beryllium oxide. Handle and dispose iaw hazmat procedures. **Test Data Document:** 80063-a3110509 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 3 pin Shelf Life: N/a **Unit Of Measure:**